Amendments to the Specification:

Beginning at page 1, line 2, please insert the following paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a divisional application of U.S. Application Serial No. 09/918,547, filed on August 1, 2001, now allowed, which claims priority from, and is a continuation-in-part of, U.S. Application No. 09/880,089 (U.S. Patent Publication No. US-2002-0043662 A1), filed June 14, 2001 and which claims the benefit of a foreign priority application filed in Japan on August 2, 2000, as Serial No. 2000-234913. This application claims priority all of these applications, and all of these applications are incorporated by reference.

Please replace the paragraph beginning at page 1, line 17 as with the following amended paragraph:

A technique has been developed for manufacturing a thin film transistor (hereinafter referred to as TFT) from a semiconductor film that has a polycrystal structure (the film is hereinafter referred to as crystalline semiconductor film) and is formed on a glass, **[[quarts]]** quartz or other substrate. A TFT formed from a crystalline semiconductor film is applied to flat panel displays, typically, liquid crystal display devices, as measures for realizing high definition image display, and is applied to monolithic displays in which a pixel portion and an integrated circuit necessary to drive the pixel portion are formed on the same substrate, as measures for realizing it.

Please replace the paragraph beginning at page 2, line 6 as with the following amended paragraph:

A crystalline semiconductor film can have a polycrystal structure if it is obtained by subjecting an amorphous semiconductor film formed on a glass, **[[quarts]]** quartz or other substrate to heat treatment or laser light irradiation for crystallization. Crystallization is known to progress from a crystal nuclear spontaneously generated in the interface between the amorphous semiconductor film and the substrate. While crystal grains in a polycrystal

structure each educe an arbitrary crystal plane, it has been found that the proportion, which the crystallization of the {111} plane requiring the minimum interface energy is educed, is high if silicon oxide is placed under the crystalline semiconductor film.

Please replace the paragraph beginning at page 2, line 14 as with the following amended paragraph:

The thickness of a semiconductor film required for TFT is about 10 to 100 nm. However, it is difficult **[[with]]** in this thickness range to control crystal orientation in the interface between the semiconductor film and a substrate that is formed from a different material due to lattice discordance or crystal nuclei generated irregularly. Also, it has been impossible to increase the grain size of each crystal grain because of mutual interference between crystal grains.

Please replace the paragraph beginning at page 5, line 1 with the following amended paragraph:

The thus formed semiconductor film contained silicon and germanium and having a crystal structure contains Group 14 (new international notation) elements in the periodic table other than silicon in a concentration of 1×10^{18} atoms/cm^3 or below. The semiconductor film contains less than 5×10^{18} nitrogen atoms per cm^3, less than 5×10^{18} carbon atoms per cm^3, and less than 1×10^{19} oxygen atoms per cm^3.

Please replace the paragraph beginning at page 18, line 10 with the following amended paragraph:

Equation 1

$$\Delta G = \Delta Gv \times V + E \times V + \gamma s \times S$$

Please replace the paragraph beginning at page 23, line 10 with the following amended paragraph:

Equation 2

$$\underline{\{101\}\ \text{orientation ratio}} = \frac{\text{the number of measurement points which angle between } \{101\} \text{ lattice plane and film surface is within allowable value}}{\text{whole points for measurement}}$$